



Description

The DMN2020LSN-7 uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 2.5V. This device is suitable for use as a Battery protection or in other Switching application.

General Features

$V_{DS} = 20V$ $I_D = 6A$

$R_{DS(ON)} < 21m\Omega$ @ $V_{GS}=4.5V$

$R_{DS(ON)} < 35m\Omega$ @ $V_{GS}=2.5V$

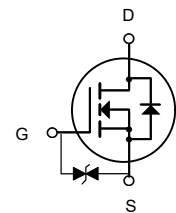
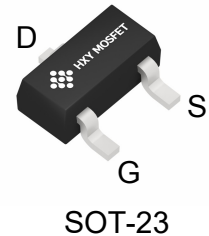
ESD=2000V HBM

Application

Battery protection

Load switch

Uninterruptible power supply



N-Channel MOSFET

Ordering Information

Product ID	Pack	Marking	Qty(PCS)
DMN2020LSN-7	SOT-23	3416	3000

Absolute Maximum Ratings ($T_A=25^{\circ}C$ unless otherwise noted)

Symbol	Parameter	Limit	Unit
V_{DS}	Drain-Source Voltage	20	V
V_{GS}	Gate-Source Voltage	± 12	V
I_D	Drain Current-Continuous	6	A
I_D	Drain Current-Continuous @ $T_A=70^{\circ}C$	3.3	A
I_{DM}	Drain Current-Pulsed (Note 1)	20.4	A
P_D	Maximum Power Dissipation	0.9	W
T_J, T_{STG}	Operating Junction and Storage Temperature Range	-55 To 150	$^{\circ}C$
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient (Note 2)	139	$^{\circ}C/W$



Electrical Characteristics (T_A=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =250uA	20	---	---	V
ΔBV _{DSS} /ΔT _J	BV _{DSS} Temperature Coefficient	Reference to 25°C, I _D =1mA	---	---	---	V/°C
R _{DS(ON)}	Static Drain-Source On-Resistance ²	V _{GS} =4.5V, I _D =5A	---	16	21	mΩ
		V _{GS} =2.5V, I _D =3A	---	25	35	
V _{GS(th)}	Gate Threshold Voltage	V _{GS} =V _{DS} , I _D =250uA	0.4	0.7	1.0	V
ΔV _{GS(th)}	V _{GS(th)} Temperature Coefficient		---	---	---	mV/°C
I _{DSS}	Drain-Source Leakage Current	V _{DS} =20V, V _{GS} =0V, T _J =25°C	---	---	1	uA
		V _{DS} =20V, V _{GS} =0V, T _J =100°C	---	---	100	
I _{GSS}	Gate-Source Leakage Current	V _{GS} =±10V, V _{DS} =0V	---	---	±10	nA
g _{fs}	Forward Transconductance	V _{DS} =10V, I _D =3A	---	---	---	S
R _g	Gate Resistance	V _{DS} =0V, V _{GS} =0V, f=1MHz	---	---	---	Ω
Q _g	Total Gate Charge	V _{DS} =10V, V _{GS} =4.5V, I _D =5A	---	8	---	nC
Q _{gs}	Gate-Source Charge		---	2.5	---	
Q _{gd}	Gate-Drain Charge		---	3	---	
T _{d(on)}	Turn-On Delay Time	V _{GS} =4.5V, V _{DD} =10V, R _G =3Ω, I _D =5A	---	0.5	---	ns
T _r	Rise Time		---	1	---	
T _{d(off)}	Turn-Off Delay Time		---	12	---	
T _f	Fall Time		---	4	---	
C _{iss}	Input Capacitance	V _{DS} =10V, V _{GS} =0V, f=1MHz	---	545	---	pF
C _{oss}	Output Capacitance		---	103	---	
C _{rss}	Reverse Transfer Capacitance		---	90	---	
I _S	Continuous Source Current ^{1,5}	V _G =V _D =0V, Force Current	---	---	6	A
V _{SD}	Diode Forward Voltage ²	V _{GS} =0V, I _S =6A, T _J =25°C	---	---	1.2	V

Notes: 1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature

2. Pulse Test: Pulse Width≤300μs, Duty Cycle≤0.5%



Typical Characteristics

Figure 1: Output Characteristics

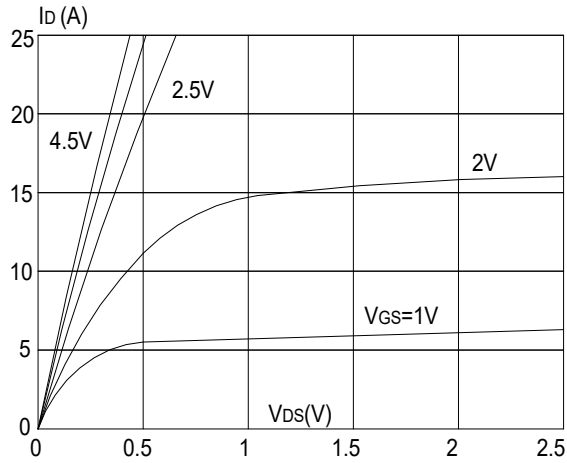


Figure 2: Typical Transfer Characteristics

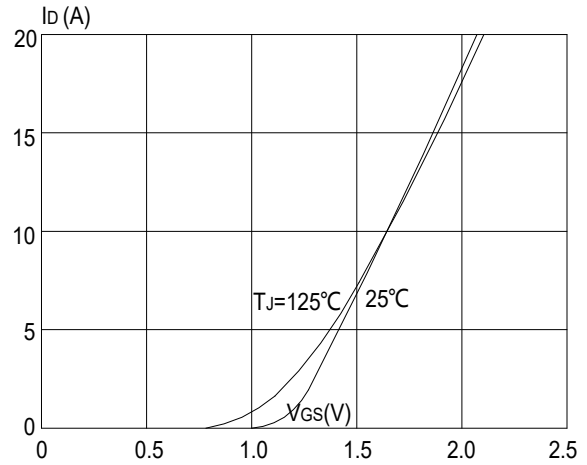


Figure 3: On-resistance vs. Drain Current

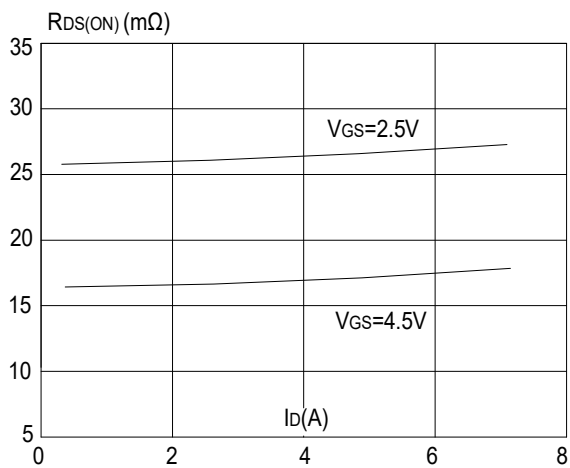


Figure 4: Body Diode Characteristics

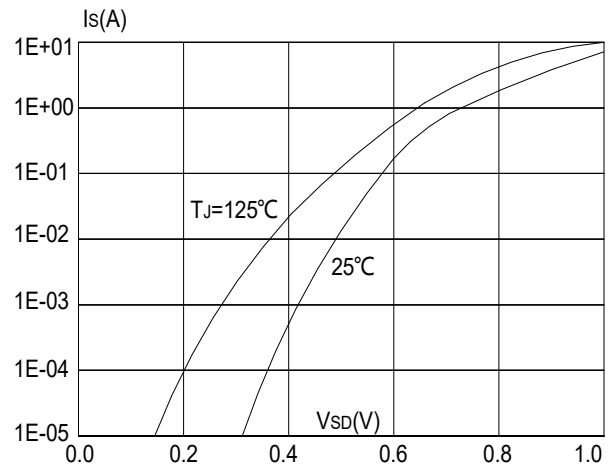


Figure 5: Gate Charge Characteristics

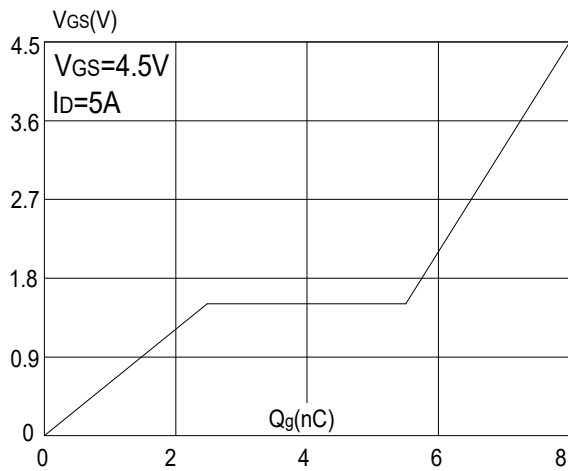


Figure 6: Capacitance Characteristics

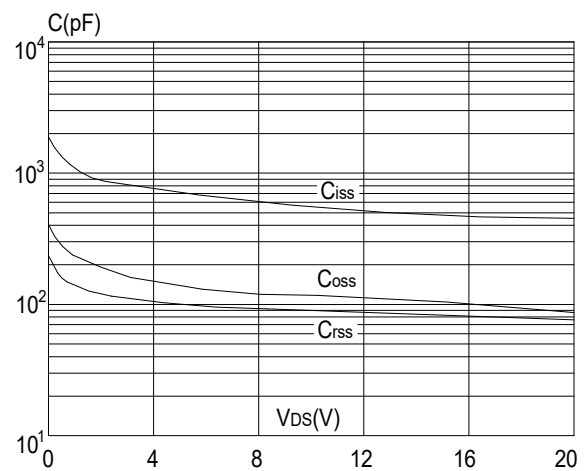




Figure 7: Normalized Breakdown Voltage vs. Junction Temperature

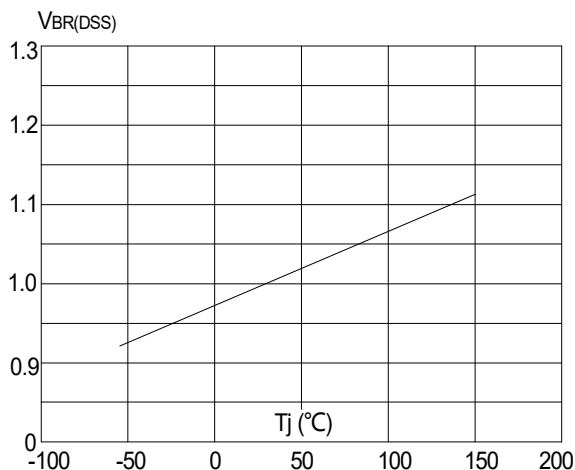


Figure 8: Normalized on Resistance vs. Junction Temperature

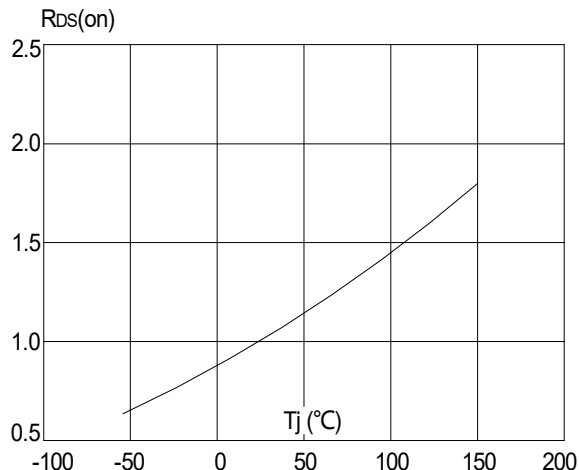


Figure 9: Maximum Safe Operating Area

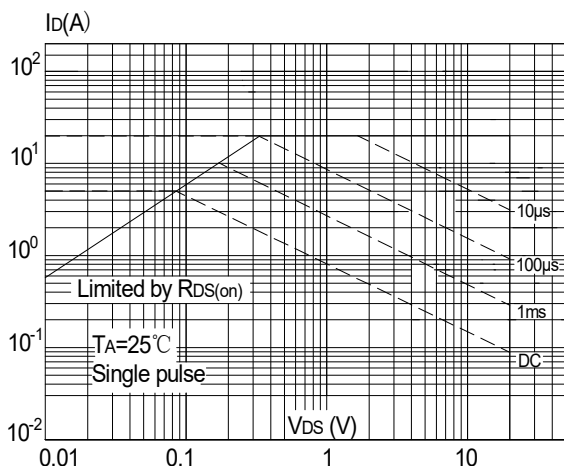


Figure 10: Maximum Continuous Drain Current vs. Ambient Temperature

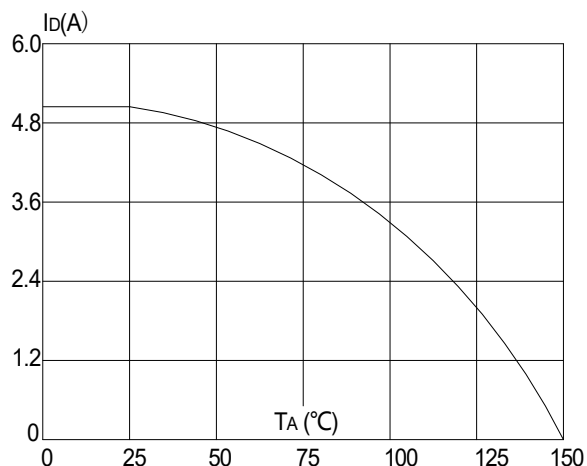
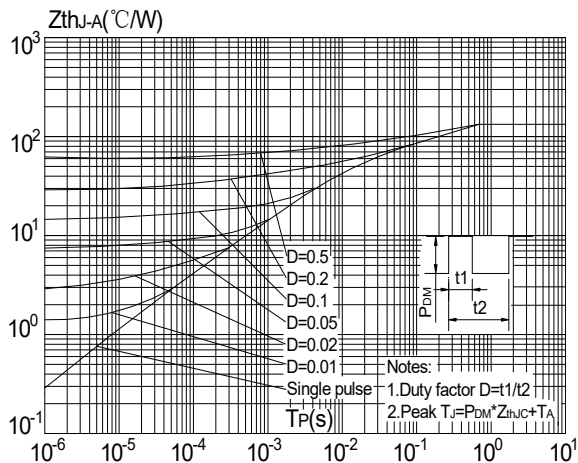
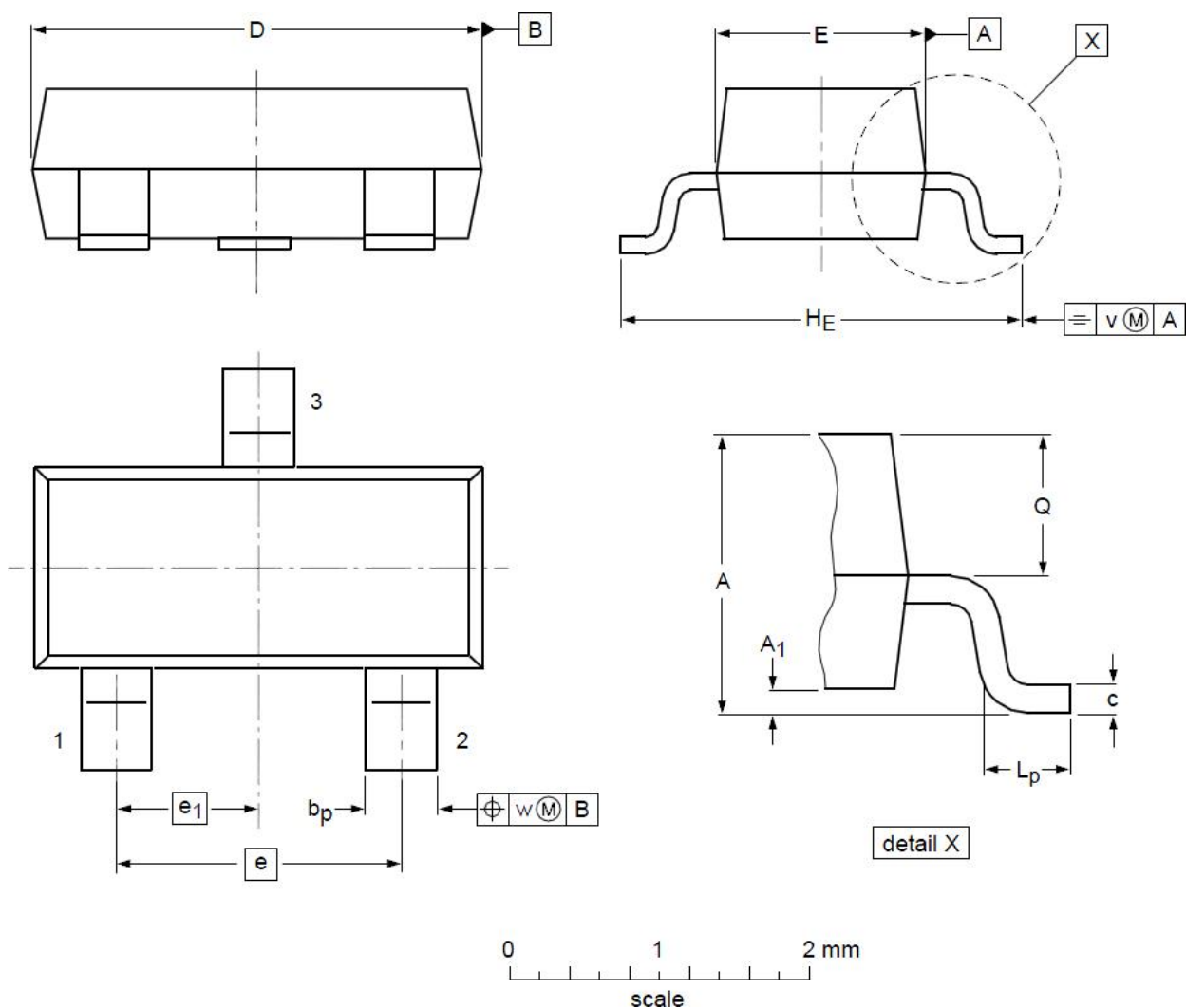


Figure.11: Maximum Effective Transient Thermal Impedance, Junction-to-Ambient





SOT-23 Package Outline Dimensions



DIMENSIONS (unit : mm)

Symbol	Min	Typ	Max	Symbol	Min	Typ	Max
A	0.90	1.01	1.15	A ₁	0.01	0.05	0.10
b _p	0.30	0.42	0.50	c	0.08	0.13	0.15
D	2.80	2.92	3.00	E	1.20	1.33	1.40
e	--	1.90	--	e ₁	--	0.95	--
H _E	2.25	2.40	2.55	L _p	0.30	0.42	0.50
Q	0.45	0.49	0.55	v	--	0.20	--
w	--	0.10	--				



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